

## Schottky Diodes: MNM 200 Series

# Medium Barrier Schottky Mixer Diodes

## Description

The **MicroMetrics** MNM 200 series of Medium Barrier Schottky diodes are metal semiconductor junction devices that have a typical short reverse recovery time. This allows their use at high microwave frequencies when the performance of the n-type may be reduced. The forward I-V of schottky diodes is determined by the junction metal used. For every different metal selection there is a different forward voltage characteristic or "Barrier Height". These devices are best suited for applications through 26 GHz.

## Applications

Medium Barrier Schottky Mixer diodes are ideally suited for use in mixers, doublers and modulators.

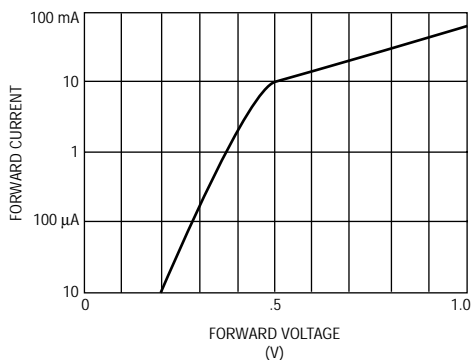
## Features

- Multi-Junction Chips
- Low 1/F Noise
- Small Junction Capacitance

## Packaging

- Chip, Glass, Ceramic, Beam Lead

## Typical Performance



## Electrical Characteristics

Breakdown Voltage @10 $\mu$ A MIN (V)	Forward Voltage @1 mA MAX (V)	Junction Capacitance @0 Vdc 1 MHz TYP (pF)	Series Resistance @5 mA TYP (Ohms)	Tangential Signal Sensitivity TYP (dB)	Part Number
3.0	0.35	0.08	15.0	-52	MNM200
3.0	0.35	0.1	15.0	-50	MNM201
3.0	0.35	0.12	12.0	-48	MNM202
3.0	0.35	0.14	8.0	-45	MNM203
4.0	0.375	0.08	15.0	-52	MNM204
4.0	0.375	0.1	15.0	-50	MNM205
4.0	0.375	0.12	12.0	-48	MNM206
4.0	0.375	0.14	8.0	-45	MNM207
5.0	0.4	0.08	15.0	-52	MNM208
5.0	0.4	0.1	15.0	-50	MNM209
5.0	0.4	0.12	12.0	-48	MNM210
5.0	0.4	0.14	8.0	-45	MNM211
6.0	0.45	0.08	15.0	-52	MNM212
6.0	0.45	0.1	15.0	-50	MNM213
6.0	0.45	0.12	12.0	-48	MNM214
6.0	0.45	0.14	8.0	-45	MNM215

## Maximum Ratings

Operating Temperature	-55°C to + 150°C
Storage Temperature	-65°C to + 200°C
Power Dissipation @25°C	250mW
(derate linearly to zero at 150°C)	

